



Pin Definition:

- 1. Base 2. Collector
- 3. Emitter

PRODUCT SUMMARY

BV _{CEO}	400V
BV _{CBO}	700V
Ι _C	2A
V _{CE(SAT)}	1.1V @ I _C =1A, I _B =0.25A

Features

- Build-in Free-wheeling Diode Makes Efficient Anti-saturation • Operation
- No Need to Interest h_{FE} Value Because of Low Variable • Storage-time Spread Even Though Comer Spirit Product.
- Low Base Drive Requirement •
- Suitable for Half Bridge Light Ballast Application •

Structure

- Silicon Triple Diffused Type •
- NPN Silicon Transistor with Diode .

Ordering Information

Part No.	Package	Packing
TSC5302DCP ROG	TO-252	2.5kpcs / 13" Reel
TSC5302DCH C5G	TO-251	75pcs / Tube

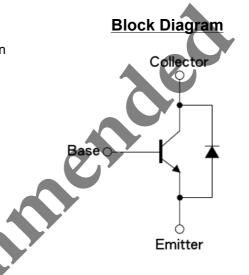
Note: "G" denote for Halogen Free Product

Absolute Maximum Ratings (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Collector-Base Voltage		V _{CBO}	700	V	
Collector-Emitter Voltage		V _{CEO}	400	V	
Emitter-Base Voltage		V _{EBO}	10	V	
Collector Current		Ι _C	2	А	
Collector Peak Current (tp <5ms)		I _{CM}	4	А	
Base Current		Ι _Β	1	А	
Base Peak Current (tp <5ms)		I _{BM}	2	А	
Tatal Dissipation @ Ta < 05%	TO-251	D	1.5	14/	
Total Dissipation @ $Tc \le 25^{\circ}C$	TO-252	P _{tot}	25	W	
Maximum Operating Junction Temperature		TJ	+150	°C	
Storage Temperature Range		T _{STG}	-65 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	Rθ _{JC}	6.25	°C/W
Junction to Ambient Thermal Resistance	RƏ _{JA}	100	°C/W





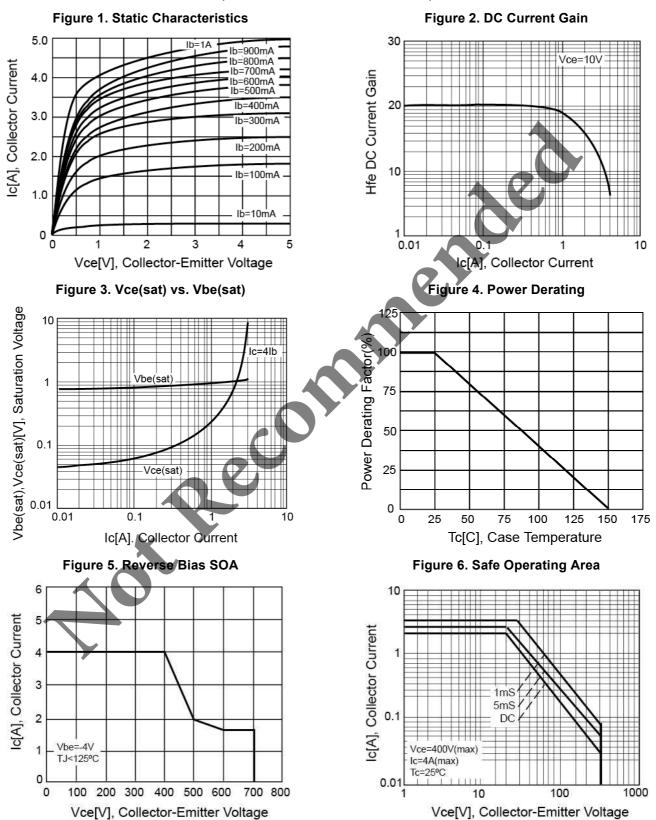
Electrical Specifications (Ta = 25°C unless otherwise noted)

ZOL

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Collector-Base Voltage	$I_{\rm C} = 1 {\rm mA}, I_{\rm B} = 0$	BV_{CBO}	700			V
Collector-Emitter Breakdown Voltage ^a	I _C = 10mA, I _E = 0	BV_{CEO}	400			V
Emitter-Base Breakdown Voltage	I _E = 1mA, I _C = 0	BV_{EBO}	10			V
Collector Cutoff Current	V _{CB} = 700V, I _E = 0	I _{CBO}			1	μA
Emitter Cutoff Current	$V_{EB} = 9V, I_{C} = 0$	I _{EBO}			1	μA
Collector-Emitter Saturation Voltage ^a	I _C =0.5A, I _B =0.1A	V _{CE(SAT)1}		(0.5	
	I _C =1A, I _B =0.25A	V _{CE(SAT)2}		1.1	1.5	V
Base-Emitter Saturation Voltage ^a	I _C =0.5A, I _B =0.1A	V _{BE(SAT)1}			1.1	
	I _C =1A, I _B =0.25A	V _{BE(SAT)2}			1.2	V
DC Current Gain	V _{CE} =5V, I _C =10mA	h _{FE} 1	10			
	V _{CE} =5V, I _C =400mA	h _{FE} 2	10		30	
	V _{CE} =5V, I _C =1A	h _{FE} 3	5			
Turn On Time	V _{CC} =250V, I _C =1A,	ton		0.15	0.3	μs
Storage Time	I _{B1} =I _{B2} =0.2A, t _p =25μs	tstg		0.5	0.9	μs
Fall Time	Duty Cycle<1%	t _f		0.2	0.4	μs
Diode						
Fall Time	I _C =1A	t⊧			800	μs
Forward Voltage Drop	I _C =1A	Vf			1.4	V

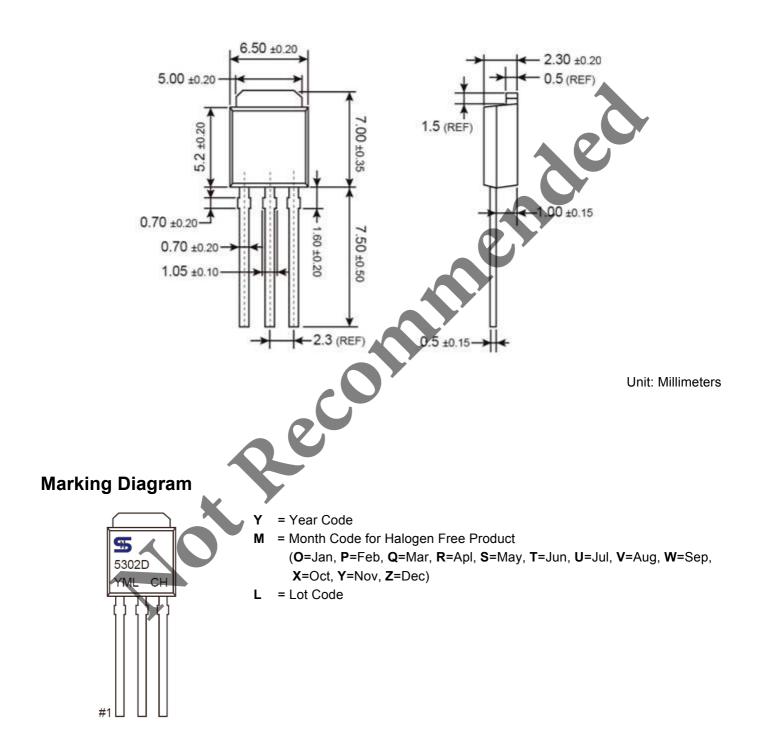


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



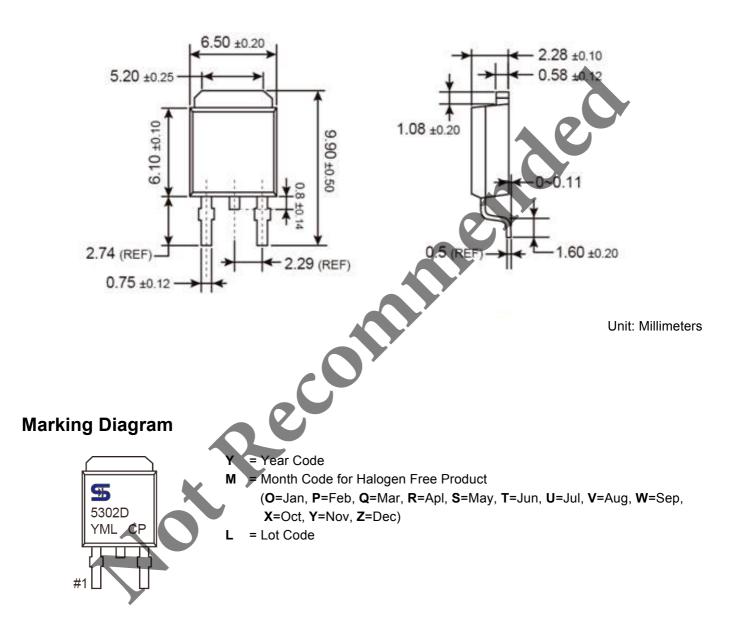


TO-251 Mechanical Drawing

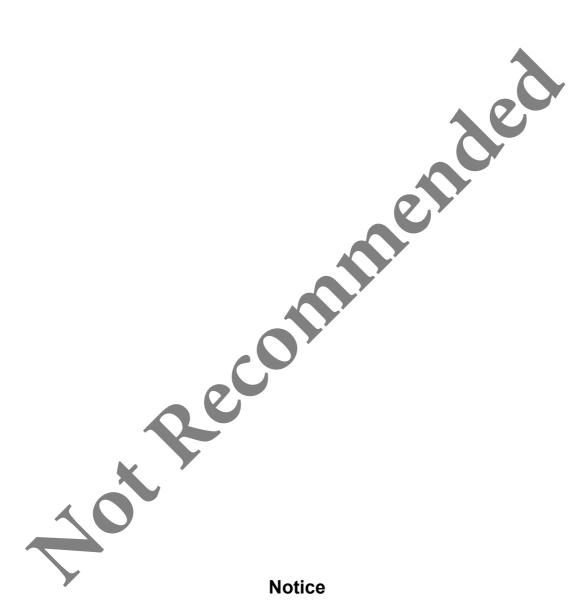




TO-252 Mechanical Drawing







Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.